**WHAT IS CLAIMED IS:**

1. A wafer producing method comprising the steps of:

planarizing an end face of a hexagonal single-crystal ingot;

forming a peel-off layer in the hexagonal single-crystal ingot by applying a first pulsed laser beam whose wavelength is transmittable through the hexagonal single-crystal ingot while positioning a focal point of the first pulsed laser beam in the hexagonal single-crystal ingot at a depth corresponding to a thickness of a wafer to be produced from the planarized end face of the hexagonal single-crystal ingot;

recording a fabrication history on the planarized end face of the hexagonal single-crystal ingot by applying a second pulsed laser beam to the hexagonal single-crystal ingot while positioning a focal point of the second pulsed laser beam in a device-free area of the wafer to be produced; and

producing a severed wafer by peeling off the wafer to be produced from the hexagonal single-crystal ingot along the peel-off layer that serves as a severance starting point.

2. The method according to claim 1, wherein

the fabrication history represents a lot number of the hexagonal single-crystal ingot, a serial number of the wafer to be produced from the hexagonal single-crystal ingot, a date on which the severed wafer is fabricated, a factory where the severed wafer is fabricated, or the type of fabrication equipment involved in the fabrication of the severed wafer.

3. The method according to claim 2, wherein

the hexagonal single-crystal ingot includes a hexagonal single-crystal SiC ingot having a first end face, a second end face opposite the first end face, a c-axis extending from the first end face to the second end face, and a c-plane perpendicular to the c-axis, the c-axis being inclined to a line normal to the first end face, and the c-plane and the first end face forming an off-angle therebetween; and

the step of forming the peel-off layer includes the steps of positioning the focal point of the first pulsed laser beam whose wavelength is transmittable through the hexagonal single-crystal SiC ingot in the hexagonal single-crystal SiC ingot at the depth corresponding to the thickness of the wafer to be produced from the first end face of the hexagonal single-crystal SiC ingot, moving the hexagonal single-crystal SiC ingot and the

focal point of the first pulsed laser beam relatively to each other in a direction perpendicular to a direction in which an off-angle is formed, thereby to separate SiC in the hexagonal single-crystal SiC ingot into Si and C and to absorb a subsequently applied first pulsed laser beam with previously formed C, thereby forming a modified region where SiC is successively separated into Si and C and a succession of cracks extending along the c-plane from the modified region, and indexing-feeding the hexagonal single-crystal SiC ingot and the focal point of the first pulsed laser beam relatively to each other by a predetermined distance in the direction in which the off-angle is formed thereby to form the peel-off layer in the hexagonal single-crystal SiC ingot.